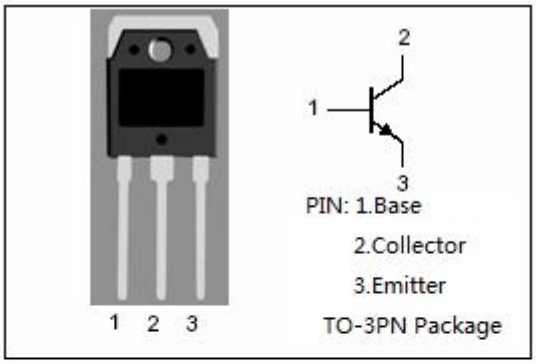
isc Silicon NPN Power Transistor 2SD731

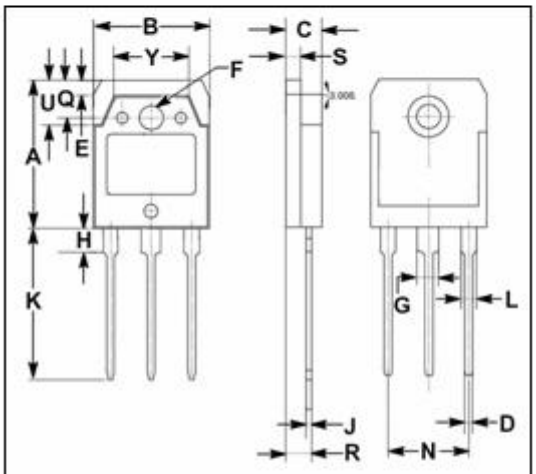


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 120V(Min)
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SB695
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	170	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA; I_B= 0	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	170			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.5	V
$V_{BE(on)}$	Base -Emitter On Voltage	I_C= 1A; V_{CE}= 5V			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 170V; I_E= 0			50	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			50	uA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	40		200	
h_{FE-2}	DC Current Gain	I_C= 5A; V_{CE}= 5V	20			
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 5V		7		MHz
C_{OB}	Output Capacitance	I_E=0; V_{CB}= 10V; f_{test}= 1.0MHz		180		pF